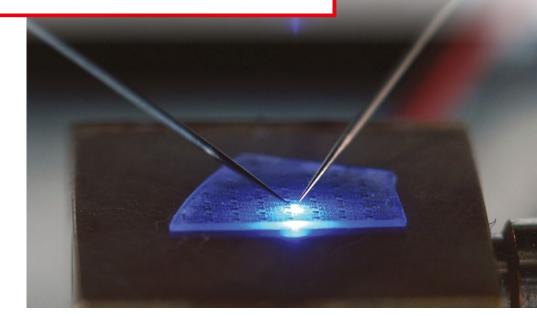


MICRO-LED ARRAYS

Tomorrow's smart lighting and display technology



Leti, technology research institute

Contact: leti.contact@cea.fr

Micro-LEDs:

Next generation for smart lighting, displays and optical communications

The next generation of smart lighting products will better control lighting intensity, shape, direction and color by integrating pixelated light sources, while display applications will be more energy efficient. GaN micro-LED technology fulfills both these projections by combining the efficiency of GaN LED direct emission and potential for manufacturing few micron size LEDs.

Key requirements:
More brightness & Smallest pitch
Micro-LED arrays meet both requirements
resulting in high performance,

low consumption, compact products.



DISPLAY

Projection, flexible, transparent, head-up & head-mounted displays

- More pixels
- Energy saving
- Brighter
- Better image quality: contrast, color saturation (true red, true green, true blue), view angle
- Robus
- More functionalities: transparent screens, foldable screens, autonomous energy harvesting

SMART LIGHTING

Automotive lighting, outdoor lighting, indoor lighting, etc.

- Better use of time, space & intensity
- Non-visual effects
- Health and wellness
- Better light usage by spatial, intensity, data and color control

OPTICAL COMMUNICATIONS

More than light: visible light communication

- For high performance computing
- Chip to chip interconnects
- Modulation bandwidth up to 1.8 GHz
- Already existing dense micro-LED infrastructure and know-how

Thermal packaging

reduction

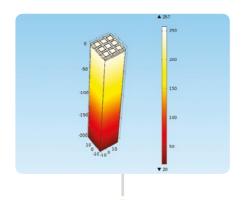
ASIC thinning

TSV

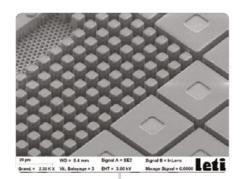
• Thermal resistance

CEA-LETI'S COMPLETE MICRO-LED ARRAY PROCESS

LETI'S VALUE PROPOSITION EMBRACES A COMPLETE DESIGN TO SYSTEM CHAIN







CHALLENGES

GaN pixelization

process flow

• Pitch reduction:

down to $\sim 1 \, \mu m$

Planar interfaces

for optimizing

hybridization

 Auto aligned process for optimizing

Hybridization

portfolio

Wide hybridization

• Cold process: micro-

tubes for hybridization

down to 10 µm pitch

• Direct heterogeneous

bonding for smaller

pitch down to 1 µm

Metal/metal or oxide/

oxide direct bonding



Color conversion

• Quantum dots

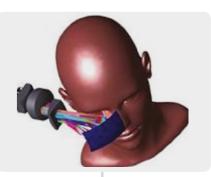
Active matrix

• 2D Quantum wells

• High current active

matrix fabrication

• Nano grain phosphors



DESIGN & SIMULATION

- Ray tracing
- Semiconductor structure simulation:
- Multiphysics simulations: Comsol
- Light extraction tools

MATERIALS & SUBSTRATES

- LED structure growth on Sapphire or other substrates
- MOCVD growth
- GaN nanowire growth
- Epitaxy on patterned substrates
- Semipolar growth

PROCESS/DIES

- Advanced LED process: VTF, TFFC
- LED array process: pixelation down to 3 µm pitch
- IC silicon active matrix for LED driving
- 10 µm pitch or less connectors
- 3D heterogeneous integration
- Bonding of LED arrays on CMOS active matrices

DEVICES

- High voltage LED chips
- Chip scale packages
- Microdisplays

MODULE

- Smart drivers
- Chip on board
- Smart sensors with embedded electronics

SYSTEMS

Smart lighting systems:

• Lifi (new advanced communication system)

Optical Systems:

- Head Mounted displays (HMDs)
- Head Up Displays (HUDs)

dedicated to R&D and industrial

Full process line dedicated to III-V compound semiconductors from 2" to 12" wafer (wafer thinning & bonding, etc.)

Device simulation & characterization platform tools: goniometer, light spectrum emission diagram, infrared thermography, etc.

Pilot line for LED die packaging: various technologies (chip to case, chip to wafer, wafer to wafer), LED matrix hybridization, etc.

INFRASTRUCTURE

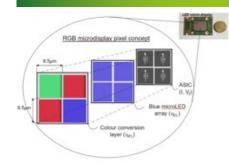
Four InGaN MOCVD epitaxy reactors process development.

MICRO-LED TECHNOLOGY EXAMPLES



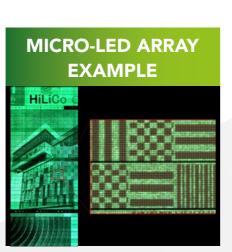
CEA-LETI MICRO-LED TECHNOLOGY CAPABILITIES FOR YOUR APPLICATION REQUIREMENTS





Building blocks for micro-LED displays

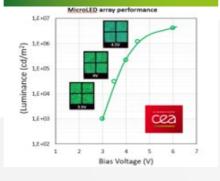
- Modelling to predict reachable white light with respect to ASIC capabilities, blue colour micro-LED efficiency and colour conversion
- ASIC design
- microLED technology
- Colour conversion
- E. Quesnel et al., J Soc Inf Display. 2020;1–14.



CEA-Leti's process flow on 200 mm wafer line

- Green epitaxy on Sapphire 100 mm or Si 200mm.
- 1750 × 1200 pixels at 9.5 μm pitch
- Array size: 11.4 mm x 16.6 mm
- Clean Sky 2 JU H2020 HILICO project

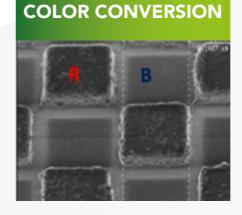
1,000,000 NITS PIXEL ARRAYS



Exceptionally high luminance

- Luminance assessment of Green micro-LED pixel arrays
- Up to 1,000,000 nits green emission!

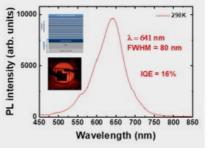
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Evaluation of colour conversion solutions

- Colour conversion nanoplatelets in solution
- Deposition with photresist
- Red pixel integration on a blue micro-LED pixel array
- Red pixel emission assessment at wafer of 80 individual passive displays
- E. Quesnel et al., Optics Express 20498, Vol. 29, 13 / 21 June 2021

NATIVE COLOUR RED MICRO-LED



Red micro-LED demonstration

- The full InGaN structure is used to realise red light emitting diodes (LEDs).
- This LED structure is composed of a partly relaxed InGaN pseudosubstrate fabricated by Soitec, namely, InGaNOS.
- A. Dussaigne et al, Journal of Applied Physics 128, 135704 (2020)



Blue micro-LED for communication

- GaN 10-µm pitch
- Wireless optical link with throughput up to 7.7 Gb/s with DCO-OFDM
- A modulation bandwidth of 1.8 GHz
- L. Maret et al, Optical Wireless Communication Conference (2022)



ABOUT LETI

Leti is a technology research institute at CEA Tech and a recognized global leader in miniaturization technologies enabling smart, energy-efficient and secure solutions. Committed to innovation, its teams create differentiating solutions for Leti's industrial partners.

By pioneering new technologies, Leti enables innovative applicative solutions that ensure competitiveness in a wide range of markets. Leti tackles critical, current global issues such as the future of industry, clean and safe energies, health and wellness, safety & security...

Leti's multidisciplinary teams deliver solid micro and nano technologies expertise, leveraging world-class pre-industrialization facilities.

For 50 years, the institute has been building long-term relationships with its industrial partners providing tailor-made solutions and a clear intellectual property policy.

Leti, technology research institute

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